

International IR Rectifier

PD - 95575

- Logic-Level Gate Drive
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

Description

Fifth Generation HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRL1004L) is available for low-profile application.

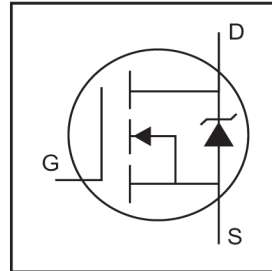
Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V} \textcircled{6}$	130 $\textcircled{5}$	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V} \textcircled{6}$	92 $\textcircled{5}$	
I_{DM}	Pulsed Drain Current $\textcircled{1} \textcircled{6}$	520	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	3.8	W
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy $\textcircled{6}$	700	mJ
I_{AR}	Avalanche Current $\textcircled{1}$	78	A
E_{AR}	Repetitive Avalanche Energy $\textcircled{1}$	20	mJ
dv/dt	Peak Diode Recovery dv/dt $\textcircled{3} \textcircled{6}$	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

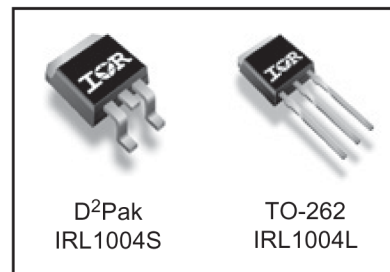
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)*	—	40	

IRL1004SPbF
IRL1004LPbF
HEXFET® Power MOSFET



$V_{DSS} = 40\text{V}$
$R_{DS(on)} = 0.0065\Omega$
$I_D = 130\text{A} \textcircled{5}$



Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	40	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.04	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.0065	Ω	V _{GS} = 10V, I _D = 78A ④
		—	—	0.009		V _{GS} = 4.5V, I _D = 65A ④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	63	—	—	S	V _{DS} = 25V, I _D = 78A⑥
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 40V, V _{GS} = 0V
		—	—	250		V _{DS} = 32V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -16V
Q _g	Total Gate Charge	—	—	100	nC	I _D = 78A
Q _{gs}	Gate-to-Source Charge	—	—	32		V _{DS} = 32V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	43		V _{GS} = 4.5V, See Fig. 6 and 13 ④⑥
t _{d(on)}	Turn-On Delay Time	—	16	—	ns	V _{DD} = 20V,
t _r	Rise Time	—	210	—		I _D = 78A,
t _{d(off)}	Turn-Off Delay Time	—	25	—		R _G = 2.5Ω,
t _f	Fall Time	—	14	—		R _D = 0.18Ω, See Fig. 10 ④⑥
L _S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C _{iss}	Input Capacitance	—	5330	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1480	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	320	—		f = 1.0MHz, See Fig. 5④⑥

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)②	—	—	130⑤	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①②	—	—	520		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 78A, V _{GS} = 0V④
t _{rr}	Reverse Recovery Time	—	78	120	ns	T _J = 25°C, I _F = 78A
Q _{rr}	Reverse Recovery Charge	—	180	270	nC	di/dt = 100A/μs④⑥
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T_J = 25°C, L = 0.23mH
R_G = 25Ω, I_{AS} = 78A. (See Figure 12)
- ③ I_{SD} ≤ 78A, di/dt ≤ 370A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handling of the package refer to Design Tip # 93-4
- ⑥ Uses IRL1004 data and test conditions

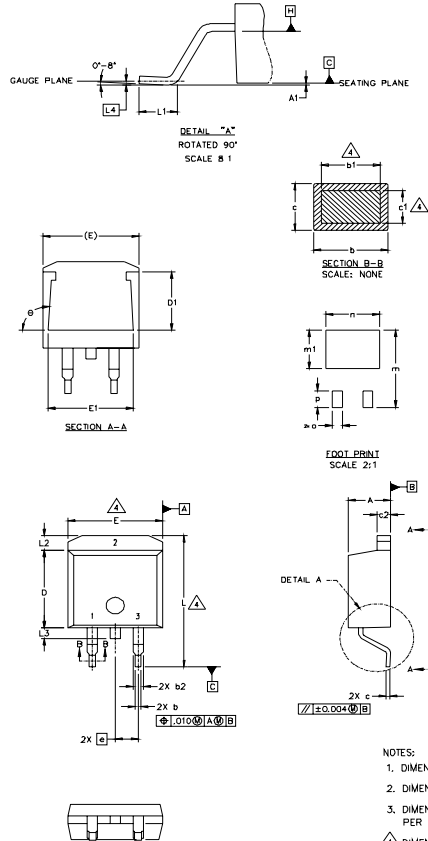
* When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

IRL1004S/LPbF

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D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	3
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54	BSC	.100	BSC	
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25	BSC	.010	BSC	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1 - GATE	1 - GATE	1 - ANODE *
2 - DRAIN	2 - COLLECTOR	2 - CATHODE
3 - SOURCE	3 - EMITTER	3 - ANODE

* PART DEPENDENT.

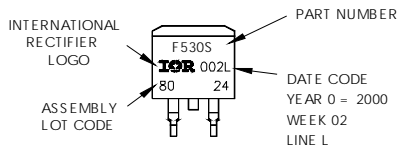
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
- CONTROLLING DIMENSION: INCH.

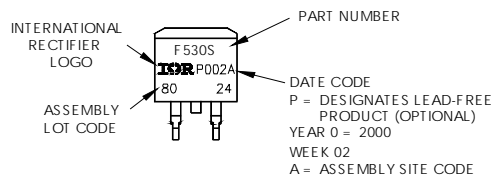
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"



OR

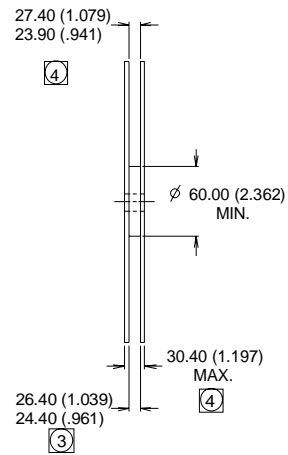
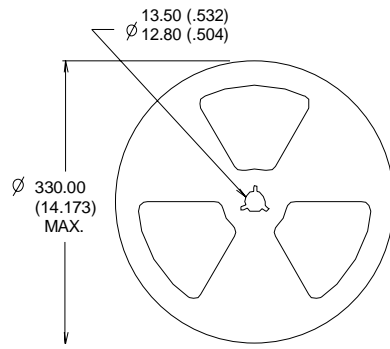
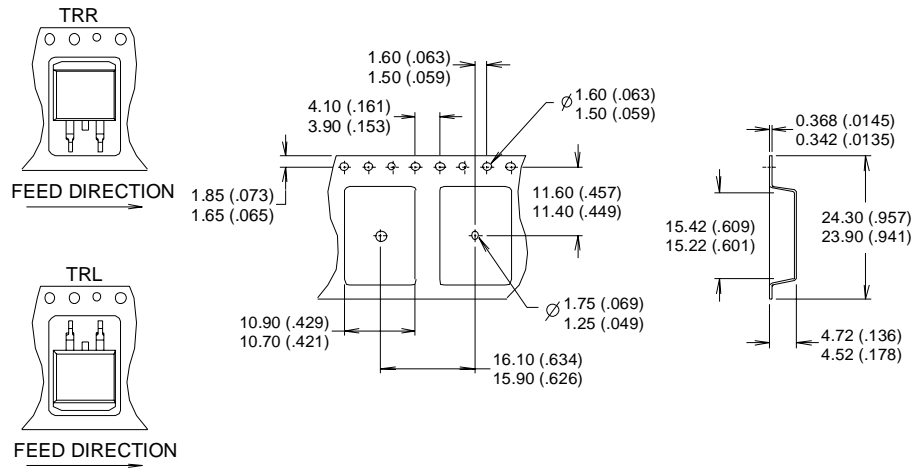


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D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.

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